



## PLD904-4-T TECHNICAL DATA

### Pulsed Infrared Laser Diode

Structure: **MOCVD**  
Lasing wavelength: **904 nm**  
Peak power: **4 W**  
Package: **TO-18T**



#### Maximum Ratings (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Peak Output Power	$P_o$	4	W
Operation Case Temperature	$T_c$	-30 .. +100	°C
Storage Temperature	$T_{STG}$	-60 .. +100	°C

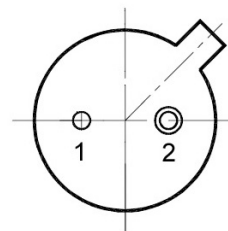
#### Optical-Electrical Characteristics (Tc = 25°C), Pulselength 50 ns, 1 kHz

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Threshold Current	$I_{th}$	pulsed mode	150	250	350	mA
Peak Current	$I_p$	$P_o = 4 W$	-	-	5	A
Peak Voltage	$V_p$	$P_o = 4 W$	-	-	6	V
Lasing Wavelength	$\lambda_p$	$P_o = 4 W$	895	904	915	nm
Emitting Aperture	$A_E$	$P_o = 4 W$	-	75 x 1	-	$\mu m^2$
Beam Divergence	$\theta_{//}$	$P_o = 4 W$	8	10	11	°
Beam Divergence	$\theta_{\perp}$	$P_o = 4 W$	30	40	50	°
Duty Factor	D	$P_o = 4 W$	-	0.1	-	%

#### Pin layout:



- 1.) laser diode cathode
- 2.) laser diode anode



Bottom View

\* Case and Pin no.1 are common



*Drawing:*

